

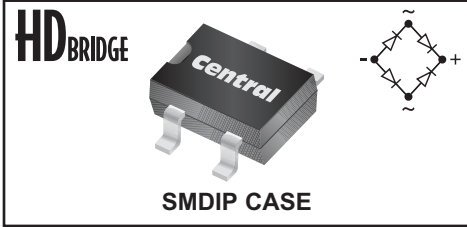
**CBRSDSH2-100**  
**SURFACE MOUNT SILICON**  
**HIGH DENSITY**  
**2.0 AMP**  
**SCHOTTKY BRIDGE RECTIFIER**



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CBRSDSH2-100 is a full wave bridge rectifier mounted in a durable epoxy surface mount case, utilizing glass passivated chips.



**MARKING: FULL PART NUMBER**

**FEATURES:**

- High 2.0A Current Rating
- Low  $V_F$  Schottky Diodes (700mV MAX @  $I_F=2.0A$ )

**MAXIMUM RATINGS:** ( $T_A=25^\circ C$  unless otherwise noted)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	$V_{RRM}$	100	V
DC Blocking Voltage	$V_R$	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	V
Average Forward Current ( $T_A=75^\circ C$ )	$I_O$	2.0	A
Peak Forward Surge Current (8.3ms)	$I_{FSM}$	110	A
Operating Junction Temperature	$T_J$	-50 to +125	$^\circ C$
Storage Temperature	$T_{stg}$	-50 to +150	$^\circ C$

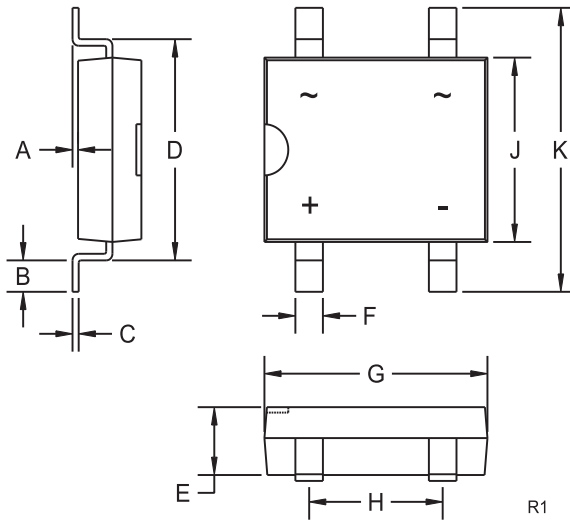
**ELECTRICAL CHARACTERISTICS PER DIODE:** ( $T_A=25^\circ C$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
$I_R$	$V_R=100V$	1.0	50	$\mu A$
$V_F$	$I_F=2.0A$	650	700	mV
$C_J$	$V_R=4.0V, f=1.0MHz$	280	500	pF

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**SMDIP CASE - MECHANICAL OUTLINE**



<b>DIMENSIONS</b>				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.008	0.10	0.20
B	0.040	0.060	1.02	1.52
C	0.009		0.23	
D	0.290	0.310	7.37	7.87
E	0.086	0.098	2.18	2.49
F	0.038	0.042	0.97	1.07
G	0.316	0.335	8.03	8.51
H	0.195	0.205	4.95	5.21
J	0.245	0.255	6.22	6.48
K	0.360	0.410	9.14	10.41

SMDIP (REV: R1)

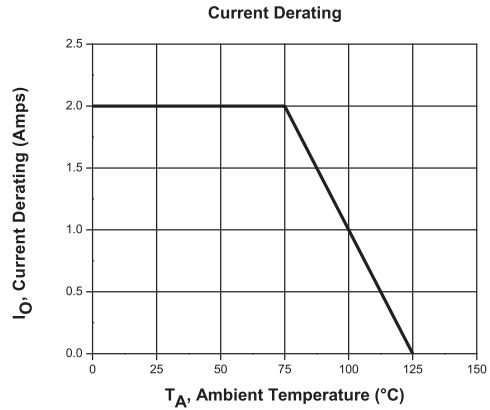
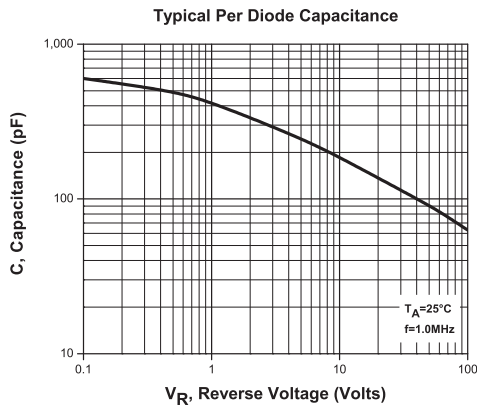
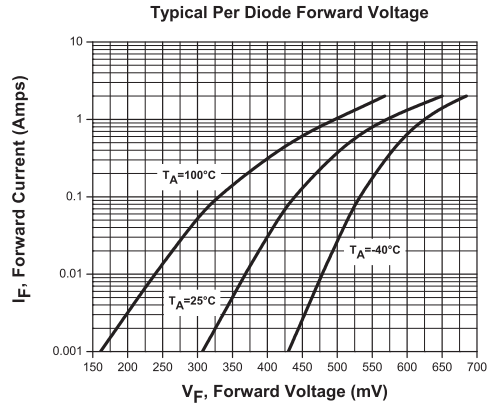
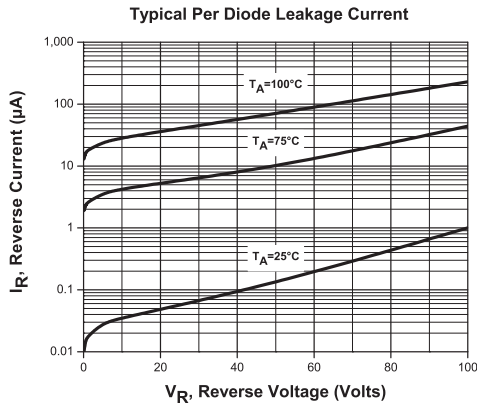
**MARKING: FULL PART NUMBER**

R3 (4-January 2013)

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**TYPICAL ELECTRICAL CHARACTERISTICS**



R3 (4-January 2013)